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Kind regards,

Team Nexperia

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

Rev. 02 — 2 September 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages

Table 1. Product overview

Type number	Package		NPN/PNP	NPN/NPN
	NXP	JEITA	complement	complement
PEMB30	SOT666	-	PEMD30	PEMH30
PUMB30	SOT363	SC-88	PUMD30	PUMH30

Reduces pick and place costs

and BC857BV

Cost-saving alternative for BC857BS

1.2 Features

- 100 mA output current capability
 Reduces component count
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



006aaa268

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

2. Pinning information

Table 3.	Pinning					
Pin	Description	Simplified outline	Symbol			
1	GND (emitter) TR1					
2	input (base) TR1	6 5 4				
3	output (collector) TR2					
4	GND (emitter) TR2					
5	input (base) TR2					
6	output (collector) TR1	001aab555	R1			
			1 2 3			

3. Ordering information

Table 4.	Ordering information
----------	----------------------

Type number	Package		
	Name	Description	Version
PEMB30	-	plastic surface-mounted package; 6 leads	SOT666
PUMB30	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMB30	2T
PUMB30	*B2

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
Per transi	stor					
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
lo	output current			-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
Per device)					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		[1]	-	300	mW
	SOT666		[1][2]	-	300	mW
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> _	-	625	K/W
	SOT666		[1][2] _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1][2] _	-	416	K/W

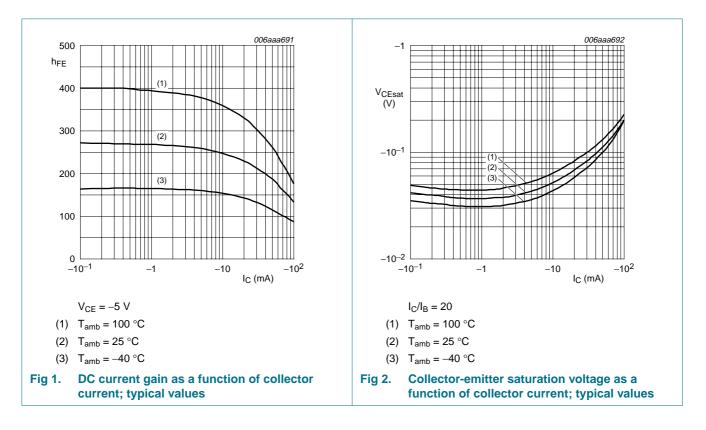
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

7. Characteristics

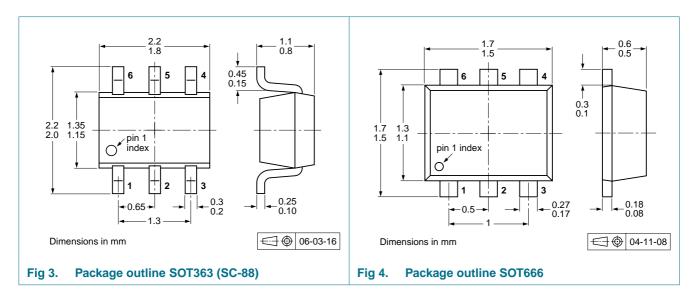
Table 8. $T_{amb} = 25$	Characteristics °C unless otherwise spec	ified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	-100	nA
I _{CEO} collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ	
	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A};$ T _j = 150 °C	-	-	-50	μA	
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_C = -20 mA	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10$ mA; $I_{B} = -0.5$ mA	-	-	-150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz	-	-	3	pF



PEMB30_PUMB30_2
Product data sheet

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

8. Package outline



9. Packing information

Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number Package		Description	Packi	Packing quantity			
			3000	4000	8000	10000	
PEMB30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-	
		4 mm pitch, 8 mm tape and reel	-	-115	-	-	
PUMB30	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165	

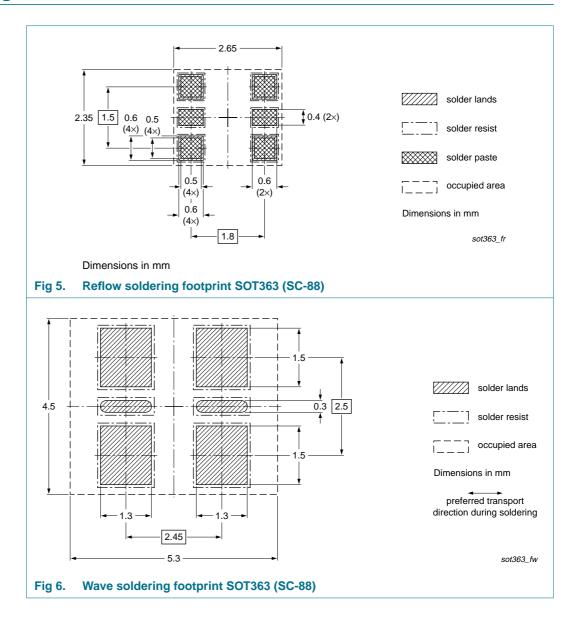
[1] For further information and the availability of packing methods, see Section 13.

[2] T1: normal taping

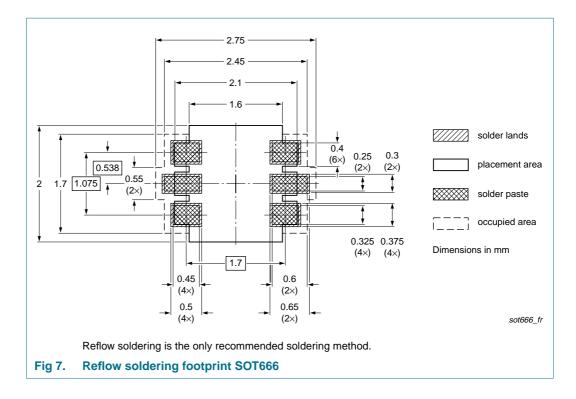
[3] T2: reverse taping

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

10. Soldering



PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open



PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMB30_PUMB30_2	20090902	Product data sheet	-	PEMB30_PUMB30_1		
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 					
	 Figure 3 "Package outline SOT363 (SC-88)": updated Figure 5 "Boffow coldaring factorint SOT262 (SC 89)": updated 					
	 Figure 5 "Reflow soldering footprint SOT363 (SC-88)": updated 					
	 Figure 6 "Wave soldering footprint SOT363 (SC-88)": updated 					
	Figure 7 "Researching of the second secon	eflow soldering footprint SC	T666": updated			
PEMB30 PUMB30 1	20060331	Product data sheet				

PEMB30_PUMB30_2
Product data sheet

PNP/PNP double resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMB30_PUMB30_2
Product data sheet

NXP Semiconductors

PEMB30; PUMB30

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

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Date of release: 2 September 2009 Document identifier: PEMB30_PUMB30_2

